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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/628,198	07/28/2003	Young-Joon Park	TI-35623	6116
23494	7590	02/21/2006	EXAMINER	
TEXAS INSTRUMENTS INCORPORATED P O BOX 655474, M/S 3999 DALLAS, TX 75265			CHAMBLISS, ALONZO	
		ART UNIT	PAPER NUMBER	
		2814		

DATE MAILED: 02/21/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

(60)

Office Action Summary	Application No.	Applicant(s)	
	10/628,198	PARK ET AL.	
	Examiner	Art Unit	
	Alonzo Chambliss	2814	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 22 December 2005.

2a) This action is FINAL. 2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 1-8 is/are pending in the application.

4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5) Claim(s) _____ is/are allowed.

6) Claim(s) 1,3 and 5-8 is/are rejected.

7) Claim(s) 2 and 4 is/are objected to.

8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a) All b) Some * c) None of:

1. Certified copies of the priority documents have been received.
2. Certified copies of the priority documents have been received in Application No. _____.
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892)

2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
 Paper No(s)/Mail Date _____

4) Interview Summary (PTO-413)
 Paper No(s)/Mail Date. _____

5) Notice of Informal Patent Application (PTO-152)

6) Other: _____

DETAILED ACTION

1. The amendment filed on 12/22/05 has been made of record in the application.

Response to Arguments

2. Applicant's arguments filed 12/22/05 have been fully considered but they are not persuasive.

In regards to Park-Uzoh both failing to disclose " depositing a second layer of copper grains having a second initial grain size over the first layer of copper grains having the first initial grain size. Park discloses depositing a second layer of copper grains having a second initial grain size over the first layer of copper grains having the first initial grain size (see col. 5 lines 49-62 and col. 6 lines 30-48). The language " having said first initial grain size " does mean that annealing process cannot take place. In fact the claims are so limited in scope to recite that **a first layer of copper grains still having the first initial grain size and there is not anneal step between the formation of the first and second layer of copper grains**. Thus, Park does not teach away from the claimed invention.

In response to Applicant's argument that there is no suggestion to combine the references, the Examiner recognizes that references cannot be arbitrarily combined and that there must be some reason why one skilled in the art would be motivated to make the proposed combination of primary and secondary references. *In re Nomiya*, 184 USPQ 607 (CCPA 1975). However, there is no requirement that a motivation to make the modification be expressly articulated. The test for combining references is what the

combination of disclosures taken as a whole would suggest to one of ordinary skill in the art. *In re McLaughlin*, 170 USPQ 209 (CCPA 1971). References are evaluated by what they suggest to one versed in the art, rather than by their specific disclosures *In re Bozek*, 163 USPQ 545 (CCPA) 1969. In this case, Park discloses the claimed invention with the exception of annealing the semiconductor wafer after the step of depositing a second layer of copper grains. Uzoh et al. discloses a method of manufacturing copper interconnects on a semiconductor wafer that comprises forming a layer of patterned dielectric material 104, the patterned dielectric material defining spaces for the copper interconnects (col. 4, lines 44-47); depositing a copper seed layer 112 over the layer of patterned dielectric material (col. 4, lines 51-56); filling the patterned dielectric layer with copper (col. 4, lines 40-44); and annealing the semiconductor wafer after the deposition of the copper layer is completed, wherein the semiconductor wafer is annealed after the completed deposition of the copper layer for the disclosed intended purpose that annealing the structure after an initial chemical mechanical polishing step results in a stabilized structure and minimizing the tensile stress on the plated structures. Thus, it would have been obvious to one of ordinary skill in the art at the time the invention was made to anneal the semiconductor wafer of Park et al. after the step of depositing a second layer of copper grains, and even after the copper interconnects are filled for the disclosed intended purpose of Uzoh et al. of annealing the structure after an initial chemical mechanical polishing step results in a stabilized structure and minimizing the tensile stress on the plated structures that is characteristic of the copper interconnects.

In regards to Park failing to teaches claimed invention of independent claim 7.

Park teaches depositing at least one additional layer 130 of copper grains of differing initial grain size over the first layer of copper, the at least one additional layer of copper grains being deposited by an electroplating process (as taught in col. 6, lines 30-48, and in Fig. 8.).

In regards to claim 8, Park teaches the claimed invention since the claims are not so limited in scope to recite " step of annealing the semiconductor wafer **after** the step of depositing the second layer of copper grains.

Therefore, this action is made **final**.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

4. Claims 1, 3, 7, and 8 are rejected under 35 U.S.C. 102(e) as being anticipated by Park et al. (US 6,709,970)

Regarding claim 1, Park et al. discloses a method of manufacturing copper interconnects on a semiconductor wafer that comprises forming a layer 50 of patterned dielectric material, the patterned dielectric material defining spaces for the copper

interconnects (as taught in col. 4, lines 55-67, and in Fig. 2); depositing a copper seed layer 90 over the layer of 'patterned dielectric material (as taught in col. 5, lines 10-14, 23-30, and in Fig. 4); depositing a first layer of copper grains 110 having a first initial grain size (as taught in col. 5, lines 51-54) over the copper seed layer by an electroplating process (as taught in col. 5, lines 31-48, and in Fig. D; and depositing a second layer 130 of copper having a second initial grain size over the first layer of copper, the second layer of copper grains being deposited by an electroplating process (as taught in col. 6, lines 30-48, and in Fig. 8.)

Regarding claim 3, Park et al. discloses in col. 6, lines 30-32 that the second initial grain size is larger than the first initial grain size.

Regarding claim 7, Park et al. discloses a method of manufacturing copper interconnects on a semiconductor wafer that comprises forming a layer 50 of patterned dielectric material, the patterned dielectric material defining spaces for the copper interconnects (as taught in col. 4, lines 55-67, and in Fig. 2); depositing a copper seed layer 90 over the layer of patterned dielectric material (as taught in col. 5, lines 10-14, 23-30, and in Fig. 4); depositing a first layer of copper grains 110 having a first initial grain size (as taught in col. 5, lines 51-54) over the copper seed layer by an electroplating process (as taught in col. 5, lines 31-48, and in Fig. D; and depositing at least one additional layer 130 of copper grains of differing initial grain size over the first layer of copper, the at least one additional layer of copper grains being deposited by an electroplating process (as taught in col. 6, lines 30-48, and in Fig. 8.)

Regarding claim 8, Park et al. discloses a method of manufacturing copper

interconnects on a semiconductor wafer that comprises forming a layer 50 of patterned dielectric material, the patterned dielectric material defining spaces for the copper interconnects (as taught in col. 4, lines 55-67, and in Fig. 2); depositing a copper seed layer 90 over the layer of patterned dielectric material (as taught in col. 5, lines 10-14, 23-30, and in Fig. 4); depositing a first layer of copper grains 110 having a first initial grain size (as taught in col. 5, lines 51-54) over the copper seed layer by an electroplating process (as taught in col. 5, lines 31-48, and in Fig. D; and depositing a second layer 130 of copper having a second initial grain size over the first layer of copper, the second layer of copper grains being deposited by an electroplating process (as taught in col. 6, lines 30-48, and in Fig. 8); and annealing the semiconductor wafer (as taught in col. 5, lines 49-50.)

Claim Rejections - 35 USC § 103

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was

not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

6. Claims 5 and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Park et al. (US 6,709,970) in view of Uzoh et al. (US 6,861,354).

Park et al. discloses a method of manufacturing copper interconnects on a semiconductor wafer that comprises forming a layer 50 of patterned dielectric material, the patterned dielectric material defining spaces for the copper interconnects (as taught in col. 4, lines 55-67, and in Fig. 2/ depositing a copper seed layer 90 over the layer of patterned dielectric material (as taught in col. 5, lines 10-14, 23-30, and in Fig. 4: depositing a first layer of copper grains 110 having a first initial grain size (as taught in col. 5, lines 51-54) over the copper seed layer by an electroplating process (as taught in col. 5, lines 31-48, and in Fig. 7); and depositing a second layer 130 of copper having a second initial grain size over the first layer of copper, the second layer of copper grains being deposited by an electroplating process (as taught in col. 6, lines 30-48, and in Fig. 8), and annealing the semiconductor wafer as disclosed in col. 5, lines 49-50.

Park et al. discloses the claimed invention with the exception of annealing the semiconductor wafer after the step of depositing a second layer of copper grains.

Uzoh et al. discloses a method of manufacturing copper interconnects on a semiconductor wafer that comprises forming a layer of patterned dielectric material 104, the patterned dielectric material defining spaces for the copper interconnect col. 4, lines 44-47); depositing a copper seed layer 112 over the layer of patterned dielectric

material (col. 4, lines 51-56); filling the patterned dielectric layer with copper (col. 4, lines 40-44); and annealing the semiconductor wafer after the deposition of the copper layer is completed, wherein the semiconductor wafer is annealed after the completed deposition of the copper layer for the disclosed intended purpose that annealing the structure after an initial chemical mechanical polishing step results in a stabilized structure and minimizing the tensile stress on the plated structures. Thus, it would have been obvious to one of ordinary skill in the art at the time the invention was made to anneal the semiconductor wafer of Park et al. after the step of depositing a second layer of copper grains, and even after the copper interconnects are filled for the disclosed intended purpose of Uzoh et al. of annealing the structure after an initial chemical mechanical polishing step results in a stabilized structure and minimizing the tensile stress on the plated structures that is characteristic of the copper interconnects.

Regarding claim 6, Park et al., as modified by Uzoh et al. in col. 4, lines 28-32, discloses that the annealing step is performed within a temperature range of 150 to 4200C for a time between 5 to 300 seconds. Thus, it would have been obvious to one of ordinary skill in the art at the time the invention was made to vary the temperature and time of annealing as there is no statement denoting the criticality of the temperature and time of annealing and since the range of temperatures and range of time disclosed by Park et al. as modified by Uzoh et al. overlap with the ranges claimed by the inventors.

"In the case where the claimed ranges "overlap or lie inside ranges disclosed by the prior art" a prima facie case of obviousness exists. In re Wertheim, 541 F.2d 257, 16 USPQ 90 (CCPA 1978); In re Woodruff, 919 F.2d 1575, 16 USPQ2d 1934 (Fed. Cir. 1990) (The prior art taught carbon monoxide concentrations of "about 1-5%" while the claim was limited to "more than 5%. The court held that "about 1-5%" allowed for concentrations slightly above 5% thus the ranges overlapped." (MPEP 2144.04)

The prior art made of record and not relied upon is cited primarily to show the product of the instant invention.

Allowable Subject Matter

7. Claims 2 and 4 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The primary reason for the allowance of the claims is the inclusion of the feature of depositing at least one additional layer of copper grains of any initial grain size over the second layer of copper grains, the at least one additional layer of copper grains being deposited by an electroplating process, which is not anticipated nor rendered obvious over the prior art of record.

Conclusion

8. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning the communication or earlier communications from the examiner should be directed to Alonzo Chambliss whose telephone number is (571) 272-1927.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-7956.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system Status information for published applications may be obtained from either Private PMR or Public PMR. Status information for unpublished applications is available through Private PMR only. For more information about the PMR system see <http://pair-dkect.uspto.gov>. Should you have questions on access to the Private PMR system contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free) or EBC_Support@uspto.gov.

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